UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 7,226,513 B2 APPLICATION NO. : 10/645911 Page 1 of 1

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INVENTOR(S)

: Hisatsugu Kurita et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 10, line 1 should read as --oxidizing a silicon wafer annealed under--

Signed and Sealed this

Eighteenth Day of September, 2007

JON W. DUDAS

Director of the United States Patent and Trademark Office